#7/ Reg. for Recorded 3/15 Romano 3/6/02

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application of

Applicant	: David L. Chapek
Serial No.	: 09/605,293
Filed	: June 28, 2000
Title	: SEMICONDUCTOR DEVICES INCLUDING A LAYER OF POLYCRYSTALLINE SILICON HAVING A SMOOTH MORPHOLOGY
Docket	: MIO 0037 VA
Examiner	: N. Drew Richards
Art Unit	: 2815

CERTIFICATE OF FACSIMILE TRANSMISSION
I hereby certify that this paper is being facsimile transmitted to the Patent and Trademark Office (Fax. No. 703/872-9319) on February 21, 2002.

Julie Cope
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Assistant Commissioner for Patents
Washington, DC 20231

Sir:

REQUEST FOR RECONSIDERATION

This paper is being filed in response to the office action mailed on February 7, 2002. Reconsideration of the rejection is respectfully requested in light of the remarks below.

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REMARKS

Claim 9 has been rejected under 35 USC § 103(a) as being unpatentable over Applicant's prior art. The Examiner asserts that the specification at page 1, lines 12-22, describes a layer of silicon dioxide doped with hydrogen ions. Because a Kaufman ion source is used, the layer is **not** free of metal contaminants. Then at page 1, line 23 through page 2, line 21, certain prior patents teach the use of plasma source ion implantation (PSII) which does not use a metal grid. Thus, the Examiner asserts that one of ordinary skill in the art would know to combine the prior art references to make the present invention. The Examiner claims that the motivation to combine would be to create a layer with increased surface hardness and improved optical properties as well as avoiding metal impurities.